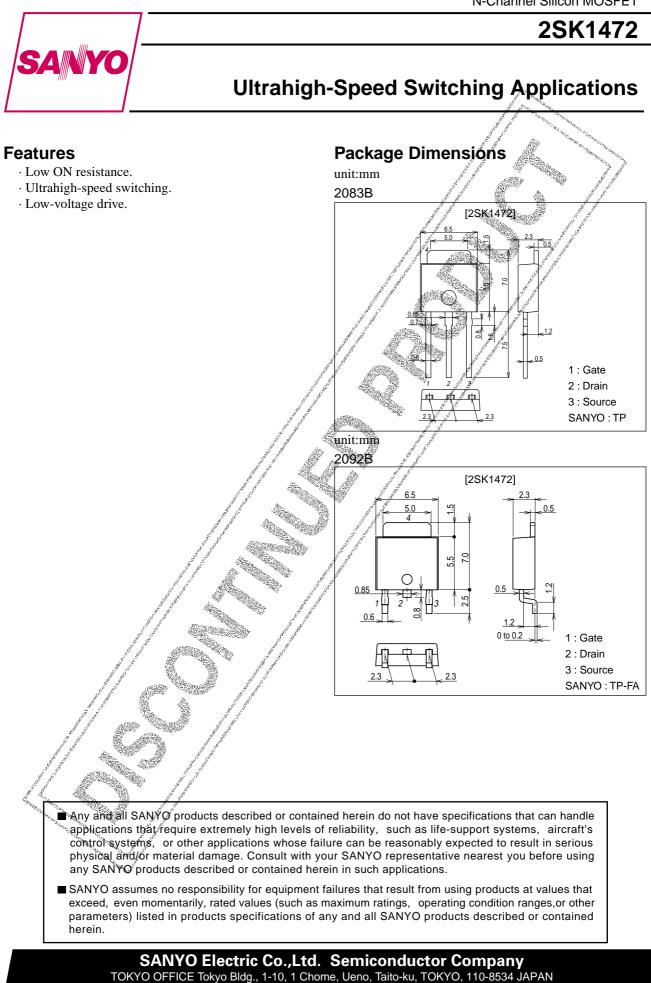
N-Channel Silicon MOSFET



## Specifications

## Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±15	V
Drain Current (DC)	۱ <sub>D</sub>		8	A
Drain Current (pulse)	I <sub>DP</sub>	PW≤10µs, duty cycle≤1%	32	A
Allowable Power Dissipation	PD		/ 🔗 🔨 1.0	W
		Tc=25°C	30	W
Channel Temperature	Tch		150	∫°C
Storage Temperature	Tstg		-55 to +150	°C
Electrical Characteristics a	t Ta = 25°C	·	Sage //	•

## **Electrical Characteristics at Ta = 25°C**

			See.	, ,	1	
Parameter	Symbol	Conditions	. min	Ratings	max	Unit
Drain-to-Source Breakdown Voltage	V <sub>(BR)</sub> DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	60	for the second s		V
Gate-to-Source Breakdown Voltage	V(BR)GSS	IG=±100μA, V <sub>DS</sub> =0	±15	AL OF REAL		V
Zero-Gate Votlage Drain Current	IDSS	V <sub>DS</sub> =60V, V <sub>GS</sub> =0	See Sta	έ.	100	μA
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0	and the second		±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.0		2.0	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =4A	5	8		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)</sub> 1	I <sub>D</sub> =4A, V <sub>GS</sub> =10V		60	80	mΩ
Static Drain-to-Source On-State Resistance	R <sub>DS(on)</sub> 2	ID=4A, VGS=4V		80	110	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f≠1MHz		950		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V/f=1MHz		250		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> ⊭20V, f=1MHz		50		pF
Turn-ON Delay Time	<sup>t</sup> d(on)	See specified Test Circuit		13		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit		30		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit		110		ns
Fall Time	t <sub>f</sub> shi shi	See specified Test Circuit		80		ns
Diode Forward Voltage	VSD	IS=8A VGS=0		1.0	1.5	V

## Switching Time Test Circuit

